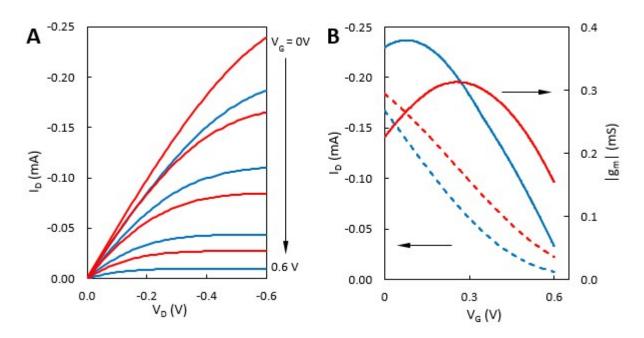


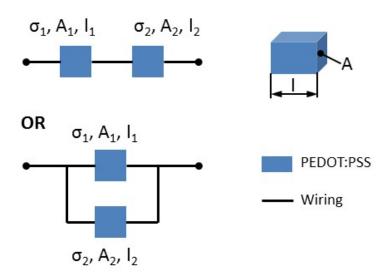
**Figure S1.** Standard three electrode measurements with SCE as reference and titanium mesh as counter electrode. Light enhancement chronoamperometry comparison of PEDOT:PSS (blue), poly(bithiophene) (red) and gold (yellow) electrodes on gold-Mylar in phosphate buffer solution (pH 7). The distance between the light source and the electrode was 2 cm and light irradiance 2400 W m<sup>-2</sup>.



**Figure S2.** OECT performance. **(A)** OECT I-V characteristics performed in dark (blue) and light (red) at 1820 W m<sup>-2</sup>. Gate voltage was varied from 0 to 0.6 V with a step of 0.2 V. Measurements performed in 0.1 M NaCl solution (pH 7). **(B)** Transfer curve (dashed line)

and associated transconductance (solid line) with (red) and without (blue) light for  $V_D = -0.6$  V.

AND



**Figure S3.** Schematics of two PEDOT:PSS channels connected in series (AND gate) and parallel (OR gate) and their properties; cross-section area, length and conductivity.

While cross-sectional area and channel length are the same for both transistors ( $A_1 = A_2 = A$ ;  $l_1 = l_2 = l$ ), conductivity values can differ and are dependent on channel doping level and light irradiance, hence

$$G_1 = \sigma_1 \frac{A}{l}; G_2 = \sigma_2 \frac{A}{l} \tag{S1}$$

The overall conductance (G) for serial connection (AND gate) is given by equation

$$\frac{1}{G} = \frac{1}{G_1} + \frac{1}{G_2} = \frac{l}{\sigma_1 A} + \frac{l}{\sigma_2 A}$$
(S2)

hence

$$G = \frac{\sigma_1 \sigma_2}{\sigma_1 + \sigma_2} \frac{A}{l} \tag{S3}$$

Similar conductance equation can be derived for parallel connection (OR gate), where

$$G = G_1 + G_2 = (\sigma_1 + \sigma_2)\frac{A}{l}$$
 (S4)

Above equations explain opto-logic gate behavior and the difference in obtained current values (fig. 3).



**Figure S4.** Picture of PEDOT:PSS channel. (A) Real scale photo of multiple channel array. (B) Microscope image of the channel.